

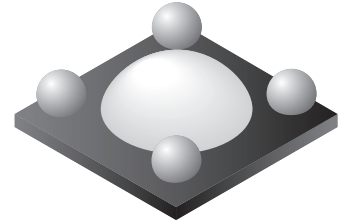
**FODB100**

**FODB101**

**FODB102**

**DESCRIPTION**

The FODB100, FODB101 and FODB102 single channel MICROCOUPLERS™ are all Pb-free, low profile miniature surface mount optocouplers in a Ball Grid Array (BGA) package. Each consists of an aluminum gallium arsenide (AlGaAs) infrared emitting diode driving a silicon phototransistor.



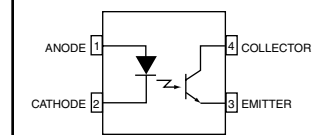
**FEATURES**

- Low profile package (1.20mm maximum mounted height)
- Land pattern allows for optimum board space savings
- High Current Transfer Ratio (CTR) at low IF
- Minimum isolation distance of 0.45mm
- High steady state isolation voltage of 2500V<sub>rms</sub>
- Data rates up to 120Kbit/s (NRZ)
- Minimum creepage distance of 2mm
- Wide operating temperature range of -40°C to +125°C
- Available in tape and reel quantities of 3000 units
- Applicable to Pb-free Infrared Ray reflow (260°C max)
- UL, C-UL approved; VDE pending

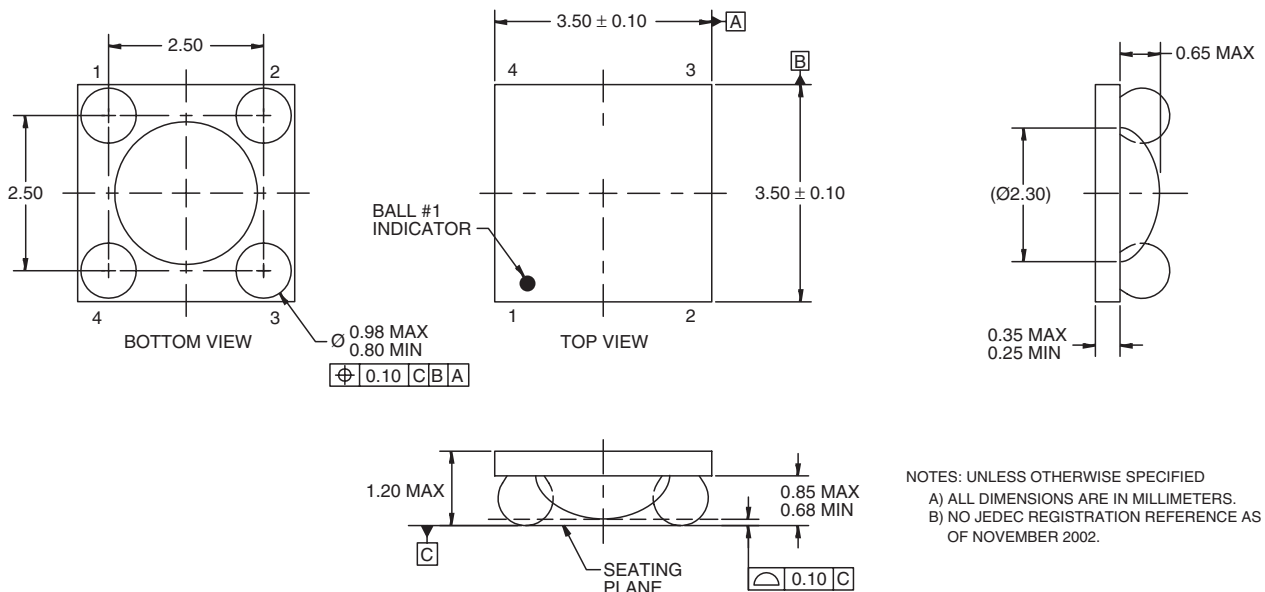
**APPLICATIONS**

- Primarily suited for DC-DC converters
- For ground loop isolation, signal to noise isolation
  - Communications – chargers, adapters
  - Consumer – appliances, set top boxes
  - Industrial – power supplies, motor control

**SCHEMATIC**



**PACKAGE DIMENSIONS**



NOTES: UNLESS OTHERWISE SPECIFIED  
 A) ALL DIMENSIONS ARE IN MILLIMETERS.  
 B) NO JEDEC REGISTRATION REFERENCE AS OF NOVEMBER 2002.

**FODB100**

**FODB101**

**FODB102**

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise specified)			
Parameter	Symbol	Value	Units
<b>TOTAL PACKAGE</b>			
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Temperature	$T_{OPR}$	-40 to +125	$^\circ\text{C}$
Junction Temperature	$T_j$	130	$^\circ\text{C}$
<b>EMITTER</b>			
Continuous Forward Current	$I_F$ (avg)	30	mA
Reverse Input Voltage	$V_R$	6	V
Power Dissipation Derate linearly (above $25^\circ\text{C}$ )	$P_D$	40	mW
		0.39	mW/ $^\circ\text{C}$
<b>DETECTOR</b>			
Continuous Collector Current		50	mA
Power Dissipation Derate linearly (above $25^\circ\text{C}$ )	$P_D$	150	mW
		1.42	mW/ $^\circ\text{C}$
Collector-Emitter Voltage	$V_{CEO}$	75	V
Emitter-Collector Voltage	$V_{ECO}$	7	V

<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ )						
<b>INDIVIDUAL COMPONENT CHARACTERISTICS</b>						
Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
<b>EMITTER</b>						
Forward Voltage	( $I_F = 2\text{ mA}$ )	$V_F$	1.0		1.5	V
Reverse Current	( $V_R = 6\text{ V}$ )	$I_R$			10	$\mu\text{A}$
<b>DETECTOR</b>						
Breakdown Voltage Collector to Emitter	( $I_C = 100\ \mu\text{A}$ , $I_F = 0$ )	$BV_{CEO}$	75			V
Emitter to Collector	( $I_E = 100\ \mu\text{A}$ , $I_F = 0$ )	$BV_{ECO}$	7			
Collector Dark Current	( $V_{CE} = 75\text{ V}$ , $I_F = 0$ )	$I_{CEO}$			100	nA
Capacitance	( $V_{CE} = 0\text{ V}$ , $f = 1\text{ MHz}$ )	$C_{CE}$		8		pF

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<b>TRANSFER CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ )						
Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Unit
Current Transfer Ratio <sup>1</sup>	( $I_F = 1 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ )	CTR	100			%
Saturated Current Transfer Ratio (Collector to Emitter)	( $I_F = 1.6 \text{ mA}$ , $V_{CE} = 0.4 \text{ V}$ )	CTR <sub>CE(SAT)</sub>	100			%
	( $I_F = 1.0 \text{ mA}$ , $V_{CE} = 0.4 \text{ V}$ )		75			
Saturation Voltage	( $I_F = 3.0 \text{ mA}$ , $I_C = 1.8 \text{ mA}$ ) ( $I_F = 1.6 \text{ mA}$ , $I_C = 1.6 \text{ mA}$ )	$V_{CE(SAT)}$			0.4	V
Rise Time (Non-Saturated)	( $I_C = 2 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ ) ( $R_L = 1\text{K}\Omega$ )	$t_r$		1		$\mu\text{s}$
Fall Time (Non-Saturated)	( $I_C = 2 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ ) ( $R_L = 1\text{K}\Omega$ )	$t_f$		5		
Propagation Delay High to Low	$I_F = 1.6 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ $R_L = 750\Omega$	$T_{PHL}$		3		$\mu\text{s}$
	$I_F = 1.6 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ $R_L = 4.7\text{K}\Omega$			12		
Propagation Delay Low to High	$I_F = 1.6 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ $R_L = 750\Omega$	$T_{PLH}$		5		$\mu\text{s}$
	$I_F = 1.6 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ $R_L = 4.7\text{K}\Omega$			19		

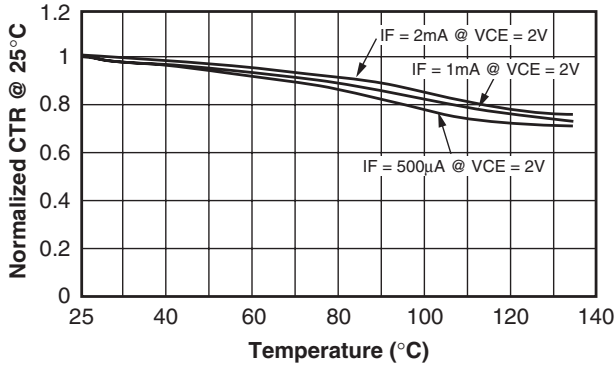
<b>ISOLATION CHARACTERISTICS</b>						
Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Unit
Steady State Isolation Voltage <sup>2</sup>	( $R_H \leq 50\%$ , $T_A = 25^\circ\text{C}$ , $t = 1 \text{ sec}$ )	$V_{ISO}$	2500			V(rms)
Resistance (input to output) <sup>2</sup>	( $V_{I-O} = 500\text{VDC}$ )	$R_{ISO}$	$10^{12}$			$\Omega$
Capacitance (input to output) <sup>2</sup>	$f = 1\text{MHz}$	$C_{ISO}$		0.3	0.5	pF

Notes:

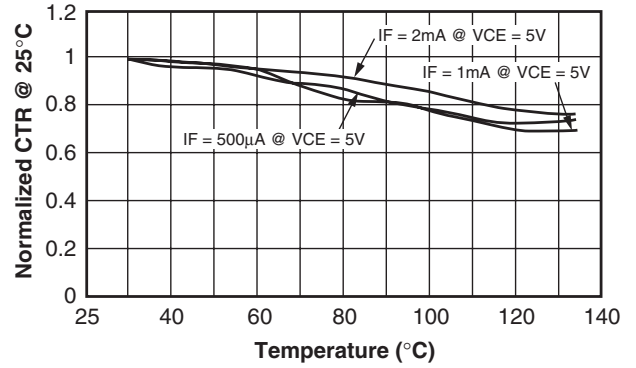
- CTR bin (FODB100 only)  
FODB101: 100% – 200%  
FODB102: 150% – 300%
- Pin 1 and Pin 2 are shorted as input and Pin 3 and Pin 4 are shorted as output.

**TYPICAL PERFORMANCE CURVES**

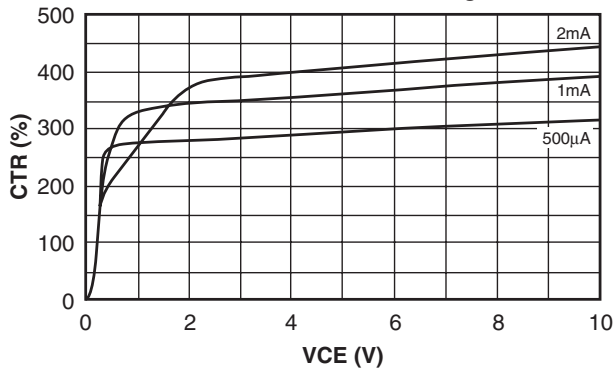
**Fig. 1 Normalized CTR vs. Temperature (VCE = 2V)**



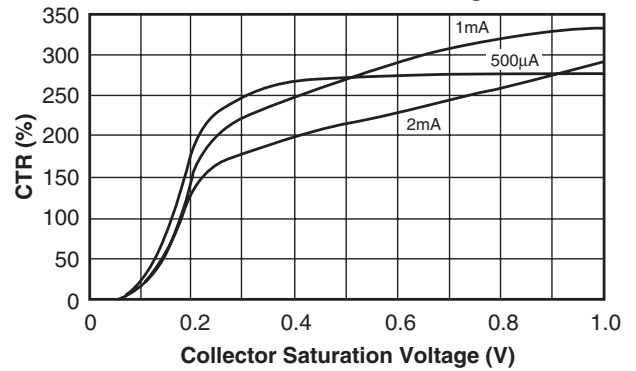
**Fig. 2 Normalized CTR vs. Temperature (VCE = 5V)**



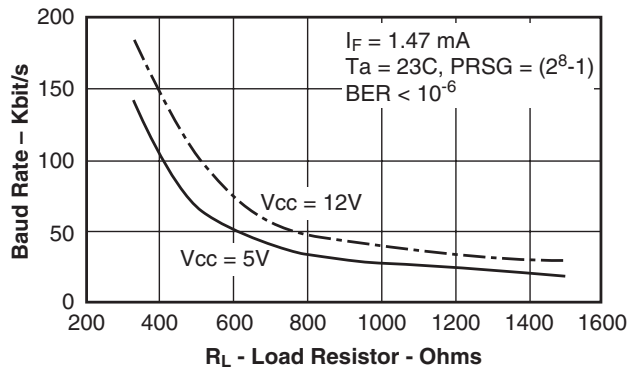
**Fig. 3 Current Transfer Ratio vs. Collector to Emitter Voltage**



**Fig. 4 Current Transfer Ratio vs. Collector Saturation Voltage**

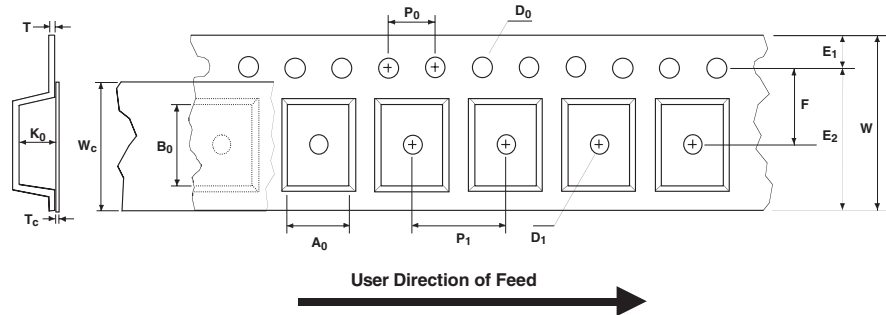


**Fig. 5 Baud Rate vs. Load Resistor**



**TAPE AND REEL SPECIFICATIONS**

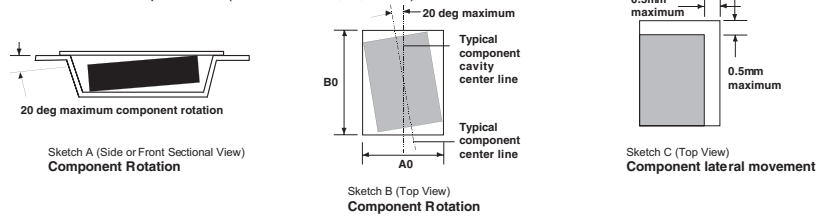
**Embossed Carrier Tape Configuration**



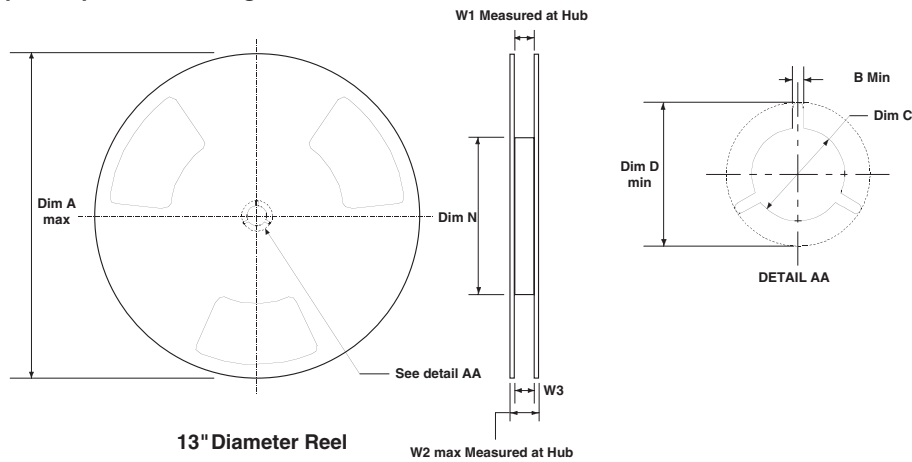
Dimensions are in millimeter

Pkg type	A <sub>0</sub>	B <sub>0</sub>	W	D <sub>0</sub>	D <sub>1</sub>	E <sub>1</sub>	E <sub>2</sub>	F	P <sub>1</sub>	P <sub>0</sub>	K <sub>0</sub>	T	W <sub>c</sub>	T <sub>c</sub>
Optocoupler (12mm)	3.80 ±0.10	3.80 ±0.10	12.0 +0.3/-0.1	1.50 +0.25/-0.00	1.50 +0.25/-0.00	1.75 ±0.10	10.25 min	5.50 ±0.05	8.0 ±0.1	4.0 ±0.1	1.40 ±0.10	0.279 ±0.02	9.2 ±0.3	0.06 ±0.02

Notes: A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



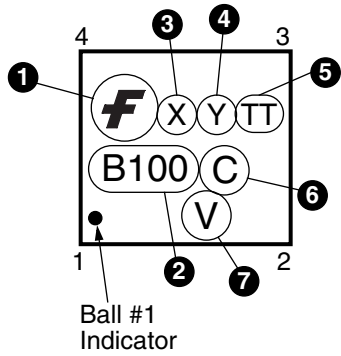
**Optocoupler Reel Configuration**



Dimension are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/-0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

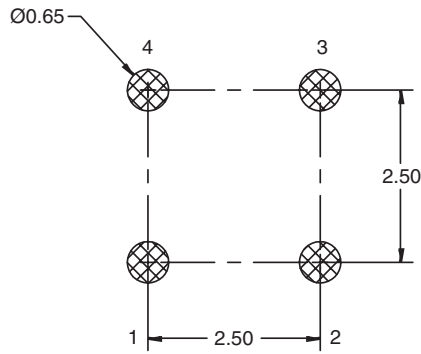
**MARKING INFORMATION**



Definitions	
1	Fairchild logo
2	Device number (FODB100)
3	One digit year code e.g. "4" for 2004
4	6-week date code character
5	Die Run Code
6	Assembly package code
7	VDE 0884 approved (Optional)

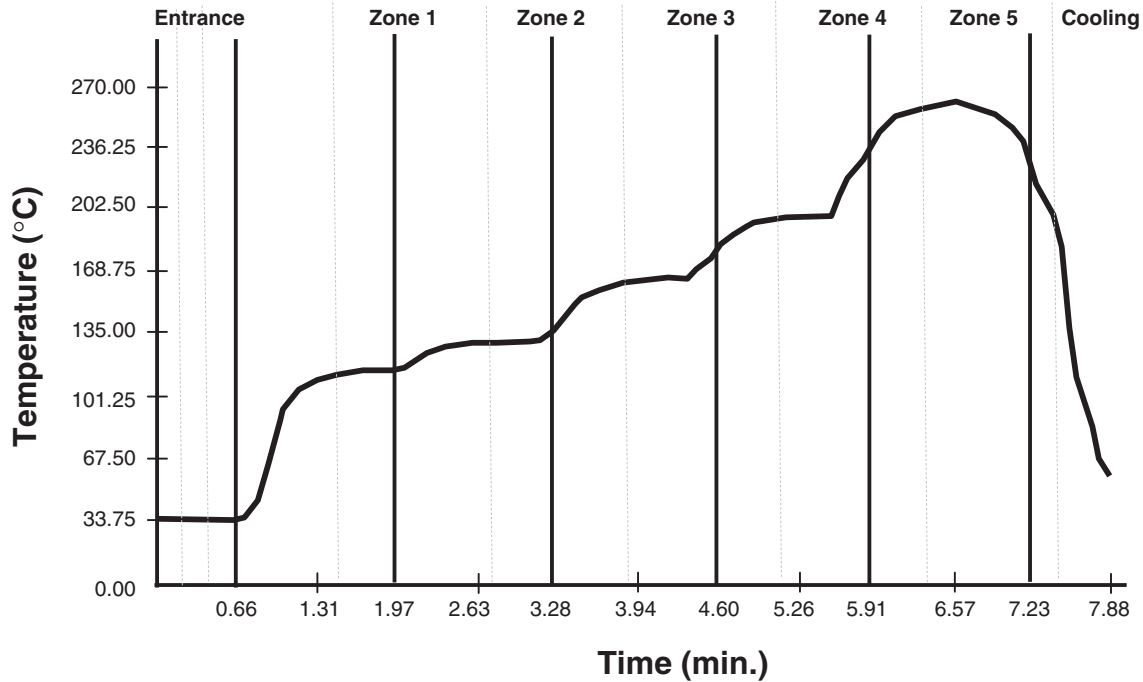
**Note:** The device number prefix of "FOD" will be omitted in the part number

**RECOMMENDED FOOTPRINT DRAWING FOR PCB LAYOUT**



- Note:**
1. All dimensions in millimeters (mm)
  2. It is recommended to use 6 mils of stencil thickness on PCB

**RECOMMENDED INFRARED REFLOW SOLDERING PROFILE**



**Reflow Profile for Pb Free**

	Convection Reflow
Average ramp-up rate (183°C to peak)	3°C/sec max
Preheat Temperature 125(±25)°C to 200°C	60-180°C
Temperature maintained above 220°C	60-150 sec
Time within 5°C of actual peak temperature	20-40 sec
Peak temperature range	260 ±5°C
Ramp down rate	6°C/sec max
Time 25°C to peak temperature	8min max

Note: Surface Mount Adhesives (SMA) isn't recommended to be used on the dome area (white dome).

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**FODB100**

**FODB101**

**FODB102**

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